

ABSTRACT OF THE DISCLOSURE

A method of manufacturing a thin film transistor and a method of manufacturing a flat panel display without increasing the number of heat treatment steps, and a thin film transistor and a flat panel display obtained by such methods are disclosed. A semiconductor region having an island shape is formed on an insulating substrate. A gate electrode is formed above the semiconductor region with a gate dielectric film being located therebetween. An impurity is implanted to the semiconductor region using the gate electrode as a mask, thereby forming source and drain regions in a self-aligned manner at both sides of a channel region. An interlayer dielectric film is formed on the gate electrode and the gate dielectric film. Thereafter, a step of activating the impurity and a step of burning the interlayer dielectric film are simultaneously performed in a single heat treatment step.